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AMENDMENTS TO THE CLAIMS

1. (Previously Presented) A method for forming an opto-electronic device, comprising:

providing a substrate and an opto-electronic layer thereon, wherein said substrate is a transparent substrate, and said transparent substrate is a member selected from the group consisting of glass, silicon, epoxy resin, poly methyl methacrylate, acrylonitrile butadiene styrene copolymer resin, polymethyl methacrylate, sapphire, polysulfones, polyethersulfones, polyetherimides, polyimides, polyamide-imide, polyphenylene sulfide and silicon-carbon thermosets;

forming an electric conductive element on said opto-electronic layer; and

forming an ohmic contact between said electric conductive element and said opto-electronic layer at a temperature lower than 250 degrees centigrade.

2. (Cancelled)

3. (Original) The method according to claim 1, wherein said ohmic contact is formed at the temperature being lower than 200 degrees centigrade.

4. (Original) The method according to claim 1, wherein said ohmic contact is formed at the temperature being higher than 100 degrees centigrade and lower than 175 degrees centigrade.

5. (Original) The method according to claim 1, wherein said ohmic contact between said electric conductive element and said opto-electronic layer is formed through a solid state growth process.

6. (Previously Presented) The method according to claim 1, wherein said electric conductive element is a material selected from the group consisting of Ni, Pd, Ge, Si, Se, Au, Ag, Pt, AuAg, AgPt, AuPt and AuAgPt.

7. (Previously Presented) The method according to claim 1, wherein said electric conductive element is a material selected from the group consisting of Ni, Pd, Zn, Be, Mg, Cd, Au, Ag, Pt, AuAg, AgPt, AuPt and AuAgPt.

8. (Previously Presented) The method according to claim 1, wherein said step for providing said opto-electronic layer on said opto-electronic layer comprises forming a plurality of semiconductor layers on said opto-electronic layer.

9. (Previously Presented) The method according to claim 8, further comprising forming said electric conductive element on a n-type doped semiconductor layer of said opto-electronic layer, wherein said electric conductive element is selected from the group consisting of Ni, Pd, Ge, Si, Se, Au, Ag, Pt, AiAg, AgPt, AuPt and AuAgPt.

10. (Previously Presented) The method according to claim 8, further comprising forming said electric conductive element on a p-type doped semiconductor layer of said opto-electronic layer, wherein said electric conductive element is selected from the group consisting of Ni, Pd, Zn, Be, Mg, Cd, Au, Ag, Pt, AuAg, AgPt, AuPt and AuAgPt.

11. (Original) The method according to claim 1, wherein said electric conductive element comprises a plurality of electrodes.

12. (Original) The method according to claim 10, wherein said step for providing said substrate and said opto-electronic layer thereon comprises:

forming a first semiconductor layer on said substrate;

forming an active layer onto said first semiconductor layer; and

forming a second semiconductor layer onto said active layer.

13. (Currently Amended) The method according to claim 12, wherein said step for forming said electric conductive element ~~comprising~~comprises:

removing portions of said first semiconductor layer and said active layer to expose portions of said second semiconductor layer; and

forming said electric conductive element on said first semiconductor layer and said exposed second semiconductor layer.

14. (Previously Presented) The method according to claim 13, wherein said first semiconductor is a n-type doped semiconductor layer.

15. (Previously Presented) The method according to claim 13, wherein said first semiconductor is a p-type doped semiconductor layer.

16. (Previously Presented) The method according to claim 15, wherein said second semiconductor layer is a n-type doped semiconductor layer.

17. (Previously Presented) The method according to claim 14, wherein said second semiconductor layer is a p-type doped semiconductor layer.

18-20. (Cancelled)

21. (Previously Presented) The method according to claim 1 ~~18~~, wherein said electric conductive element is a material selected from the group consisting of Ni, Pd, Ge, Si, Se, Au, Ag, Pt, AiAg, AgPt, AuPt and AuAgPt.

22. (Previously Presented) The method according to claim 18, wherein said electric conductive element is a material selected from the group consisting of Ni, Pd, Zn, Be, Mg, Cd, Au, Ag, Pt, AuAg, AgPt, AuPt and AuAgPt.

23. (Cancelled)

24. (Currently Amended) The method according to claim 18, wherein said step for providing said substrate comprises ~~adhereing~~ adhering said opto-electronic layer on said transparent substrate by an adhesive layer.

25. (Previously Presented) The method according to claim 24, wherein said adhesive layer is a member selected from the group consisting of epoxy resin, acrylonitrile butadiene styrene copolymer resin and polymethyl methacrylate.

26. (Previously Presented) The method according to claim 24, wherein said adhesive layer is a material selected from the group consisting of polysulfones, polyethersulfones, polyetherimides, polyimides, polyamide-imide, polyphenylene sulfide and silicon-carbon thermosets.

27. (Original) A solar cell comprising an opto-electronic device formed by a method for forming an opto-electronic device according to claim 1.

28. (Original) A light sensor comprising an opto-electronic device formed by a method for forming an opto-electronic device according to claim 1.

29. (Previously Presented) A method for forming an opto-electronic device, comprising:

providing a substrate, wherein said substrate is a transparent substrate, and said transparent substrate is a member selected from the group consisting of glass, silicon, epoxy resin, poly methyl methacrylate, acrylonitrile butadiene styrene copolymer resin, polymethyl methacrylate, sapphire, polysulfones, polyethersulfones, polyetherimides, polyimides, polyamide-imide, polyphenylene sulfide and silicon-carbon thermosets;

forming an opto-electronic layer on said substrate;

forming a transparent substrate on said opto-electronic layer and removing said substrate;

forming an electric conductive element on said opto-electronic layer; and

forming an ohmic contact between said electric conductive element and said opto-electronic layer at a temperature lower than 250 degrees centigrade.

30. (Previously Presented) The method according to claim 29, wherein said ohmic contact between said electric conductive element and said opto-electronic layer is formed by a solid state growth process.

31. (Previously Presented) The method according to claim 29, wherein said ohmic contact is formed at a temperature being lower than 200 degrees centigrade.

32. (Previously Presented) The method according to claim 29, wherein said ohmic contact is formed at a temperature being higher than 100 degrees centigrade and lower than 175 degrees centigrade.

33. (Previously Presented) The method according to claim 29, wherein said electric conductive element is a material selected from the group consisting of Ni, Pd, Ge, Si, Se, Zn, Be, Mg, Cd, Au, Ag, Pt, AuAg, AgPt, AuPt and AuAgPt.